

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	533	((electronic adj device) and (substrate near sapphire))	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:14
L2	129	1 and SOI	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:15
L3	111	2 and @ad<"20031802"	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:15
L4	4	(SOS) and inductor and groove	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:16
L5	0	(Silicon adj on adj sapphire) and inductor and groove	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:17
L6	0	(silicon adj on adj sapphire) and inductor and groove	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:17
L7	0	(silicon adj on adj sapphire)	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:17
L8	3290	(silicon-on-sapphire)	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:17
L9	208	8 and ((inductor or transistor) and (groove or window))	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:17
L10	179	9 and @ad<"20031802"	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:18
S1	37	(SOI) and inductor and groove	US-PGPUB; USPAT	OR	OFF	2006/03/17 23:16
S2	0	(silicon adj on adj insulator) and substrate near (groove or via) and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:21
S3	0	(silicon adj on adj insulator) and substrate same (groove or via) and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:37
S4	0	(silicon adj on adj insulator) and substrate same (groove or via or hole) and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:38
S5	0	(silicon adj on adj insulator) and (groove or via or hole) and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:38
S6	10	(silicon adj on adj insulator)	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:46
S7	10	"silicon on insulator"	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:47
S8	14472	SOI	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:48
S9	5711	S8 and substrate and (groove or via or hole) and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:51

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S10	510	S8 and substrate near (groove or via or hole) and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:58
S11	10	S10 and inductor	US-PGPUB; USPAT	OR	OFF	2004/09/24 12:51
S12	2	S8 and substrate near (groove or via or hole) near transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:06
S13	3476	257/347	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:06
S14	152	S13 and (groove or hole or via) near substrate	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:07
S15	2	S14 and inductor	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:07
S16	128	S14 and transistor	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:08
S17	5	S13 and substrate near membrane	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:44
S18	1	"5530266".pn.	US-PGPUB; USPAT	OR	OFF	2004/09/24 13:44
S19	1	"20040159888"	US-PGPUB; USPAT	OR	OFF	2005/04/27 15:24
S20	1	inductor and soi and (groove near substrate)	US-PGPUB; USPAT	OR	OFF	2005/04/27 15:24
S21	1	("5530266").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/16 15:05
S22	46	"5530266"	US-PGPUB; USPAT	OR	OFF	2005/10/16 15:05
S23	80	((sapphire near substrate) and insulat\$ and SOI and transistor and induct\$)	US-PGPUB; USPAT	OR	OFF	2006/03/09 10:36
S24	46	"5530266"	US-PGPUB; USPAT	OR	OFF	2006/03/09 10:36
S25	17	"5812231"	US-PGPUB; USPAT	OR	OFF	2006/03/09 10:53
S26	22544	substrate near (hole or groove or via or void or (back adj etch\$))	US-PGPUB; USPAT	OR	OFF	2006/03/09 10:54
S27	4184	S26 and insulat\$ and transistor	US-PGPUB; USPAT	OR	OFF	2006/03/09 10:54
S28	135	S27 and inductor	US-PGPUB; USPAT	OR	OFF	2006/03/09 10:54
S29	114	S28 and @ad<"20031802"	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:03
S30	738	257/622	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:03

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S31	689	S30 and substrate	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:03
S32	52632	S31 and transistor or inductor	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:04
S33	324	S31 and (transistor or inductor)	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:04
S34	311	S33 and @ad<"20031802"	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:04
S35	160	S34 and (substrate same (groove or hole or via or void))	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:07
S36	6180	(dielectric adj loss)	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:07
S37	899	S36 and ((dielectric adj loss) same substrate)	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:08
S38	101	S37 and transistor	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:09
S39	6	S38 and (transistor same substrate same (dielectric adj loss))	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:08
S40	89	S38 and @ad<"20031802"	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:17
S41	1	"20040159888"	US-PGPUB; USPAT	OR	OFF	2006/03/09 11:17
S42	1471	((substrate same sapphire) and (SOI or (silicon adj on adj insulat\$)) and (groove or window or hole or (back adj etch)) and insulat\$)	US-PGPUB; USPAT	OR	OFF	2006/03/17 14:16
S43	875	S42 and substrate same (groove or hole or window or (back adj etch))	US-PGPUB; USPAT	OR	OFF	2006/03/17 14:16
S44	708	S43 and @ad<"20031802"	US-PGPUB; USPAT	OR	OFF	2006/03/17 14:17
S45	55	S44 and (inductor or inductance)	US-PGPUB; USPAT	OR	ON	2006/03/17 14:17
S46	1	"20040159888"	US-PGPUB; USPAT	OR	ON	2006/03/17 14:22
S47	327	S44 and (groove or window)	US-PGPUB; USPAT	OR	ON	2006/03/17 14:22
S48	232	S42 and substrate near5 (groove or window)	US-PGPUB; USPAT	OR	ON	2006/03/17 14:41
S49	41	S42 and substrate near5 ((back adj etch) or (back adj side))	US-PGPUB; USPAT	OR	ON	2006/03/17 14:46
S50	137	257/447	US-PGPUB; USPAT	OR	ON	2006/03/17 15:22
S51	1	"5714790".PN.	USPAT; USOCR	OR	OFF	2006/03/17 14:53

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S52	135	257/460	US-PGPUB; USPAT	OR	ON	2006/03/17 15:22
S53	44	((transistor same inductor) and (substrate near5 sapphire))	US-PGPUB; USPAT	OR	OFF	2006/03/17 16:58
S54	76	"5539241"	US-PGPUB; USPAT	OR	OFF	2006/03/17 16:58
S55	0	((substrate near5 sapphire) same (inductor near5 transistor))	US-PGPUB; USPAT	OR	OFF	2006/03/17 19:13
S56	0	((substrate near5 sapphire) same (inductor and transistor))	US-PGPUB; USPAT	OR	OFF	2006/03/17 19:13
S57	12	((substrate near5 sapphire) and (inductor near5 transistor))	US-PGPUB; USPAT	OR	OFF	2006/03/17 19:15
S58	100	((substrate near5 sapphire) and (inductor and transistor))	US-PGPUB; USPAT	OR	OFF	2006/03/17 19:16
S59	10	"5668057"	US-PGPUB; USPAT	OR	OFF	2006/03/17 19:16